Product data sheet

## 1. Product profile

## 1.1 General description

Planar PIN diode in a SOD882D leadless ultra small plastic SMD package.

### 1.2 Features and benefits

- High speed switching for RF signals
- Low diode capacitance
- Low forward resistance
- Very low series inductance
- For applications up to 3 GHz

## 1.3 Applications

RF attenuators and switches

# 2. Pinning information

Table 1. Discrete pinning

Pin	Description	Simplified outline Symbol
1	cathode	[1]
2	anode	
		Transparent sym006 top view

<sup>[1]</sup> The marking bar indicates the cathode.

# 3. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BAP55LX	DFN1006D-2	leadless ultra small plastic package; 2 terminals; body 1 $\times$ 0.6 $\times$ 0.4 mm	SOD882D



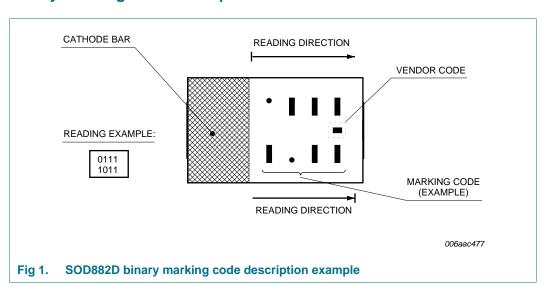
## 4. Marking

Table 3. Marking codes

Type number	Marking code <sup>[1]</sup>
BAP55LX	1111
	1101

<sup>[1]</sup> For SOD882D binary marking code description, see Figure 1.

## 4.1 Binary marking code description



# 5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0 , ,	,		
Symbol	Parameter	Conditions	Min	Max	Unit
$V_R$	reverse voltage		-	50	V
I <sub>F</sub>	forward current		-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 90 °C	-	135	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-65	+150	°C

## 6. Thermal characteristics

Table 5. Thermal characteristics

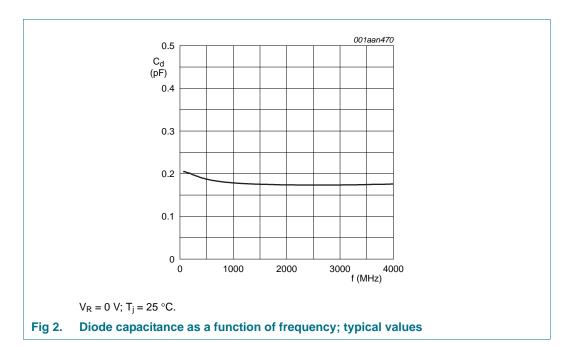
Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		78	K/W

# 7. Characteristics

Table 6. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{F}$	forward voltage	$I_F = 50 \text{ mA}$	-	0.95	1.1	V
$I_R$	reverse current	V <sub>R</sub> = 20 V	-	-	10	nA
		V <sub>R</sub> = 50 V	-	-	100	nA
C <sub>d</sub>	diode capacitance	see Figure 3; f = 1 MHz;				
		$V_R = 0 V$	-	0.28	-	pF
		$V_R = 1 V$	-	0.23	-	pF
		V <sub>R</sub> = 20 V	-	0.18	0.28	pF
$r_D$	diode forward resistance	see Figure 4; f = 100 MHz;				
		$I_F = 0.5 \text{ mA}$	-	3.3	4.5	Ω
		I <sub>F</sub> = 1 mA	-	2.2	3.3	Ω
		I <sub>F</sub> = 10 mA	-	8.0	1.2	Ω
		I <sub>F</sub> = 100 mA	-	0.5	8.0	Ω
ISL	isolation	see <u>Figure 5</u> ; V <sub>R</sub> = 0 V;				
		f = 900 MHz	-	19	-	dB
		f = 1800 MHz	-	14	-	dB
		f = 2450 MHz	-	12	-	dB
L <sub>ins</sub>	insertion loss	see Figure 6; I <sub>F</sub> = 0.5 mA;				
		f = 900 MHz	-	0.24	-	dB
		f = 1800 MHz	-	0.25	-	dB
		f = 2450 MHz	-	0.26	-	dB
L <sub>ins</sub>	insertion loss	see Figure 6; I <sub>F</sub> = 1 mA;				
		f = 900 MHz	-	0.17	-	dB
		f = 1800 MHz	-	0.18	-	dB
		f = 2450 MHz	-	0.19	-	dB
L <sub>ins</sub>	insertion loss	see Figure 6; I <sub>F</sub> = 10 mA;				
		f = 900 MHz	-	0.08	-	dB
		f = 1800 MHz	-	0.09	-	dB
		f = 2450 MHz	-	0.10	-	dB
L <sub>ins</sub>	insertion loss	see Figure 6; I <sub>F</sub> = 100 mA;				
		f = 900 MHz	-	0.05	-	dB
		f = 1800 MHz	-	0.07	-	dB
		f = 2450 MHz	-	0.08	-	dB
$\tau_{L}$	charge carrier life time	when switched from I <sub>F</sub> = 10 mA to I <sub>R</sub> = 6 mA; R <sub>L</sub> = 100 $\Omega$ ; measured at I <sub>R</sub> = 3 mA	0.225	0.27	-	μ\$
L <sub>S</sub>	series inductance	I <sub>F</sub> = 100 mA; f = 100 MHz	-	0.4	-	nH



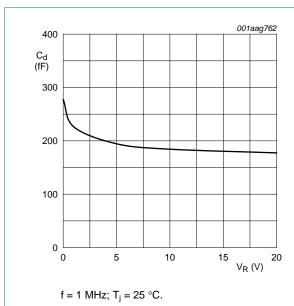


Fig 3. Diode capacitance as a function of reverse voltage; typical values

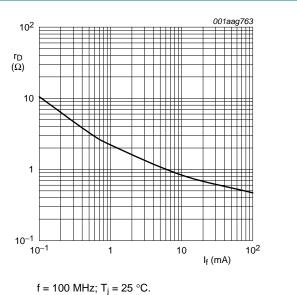
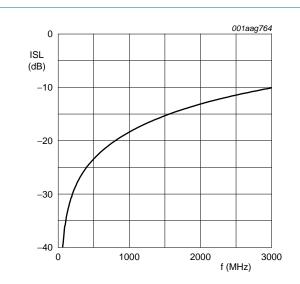


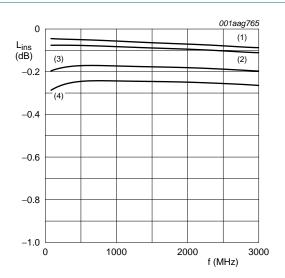
Fig 4. Forward resistance as a function of forward current; typical values



 $T_{amb}$  = 25  $^{\circ}C$ 

Diode zero biased and inserted in series with a 50  $\Omega$  stripline circuit





T<sub>amb</sub> = 25 °C

- (1)  $I_F = 100 \text{ mA}$
- (2)  $I_F = 10 \text{ mA}$
- (3)  $I_F = 1 \text{ mA}$
- (4)  $I_F = 0.5 \text{ mA}$

Diode inserted in series with a 50  $\Omega$  stripline circuit and biased via the analyzer Tee network

Fig 6. Insertion loss of the diode as a function of frequency; typical values

## 7.1 S-parameters

## 7.1.1 Diode in series configuration

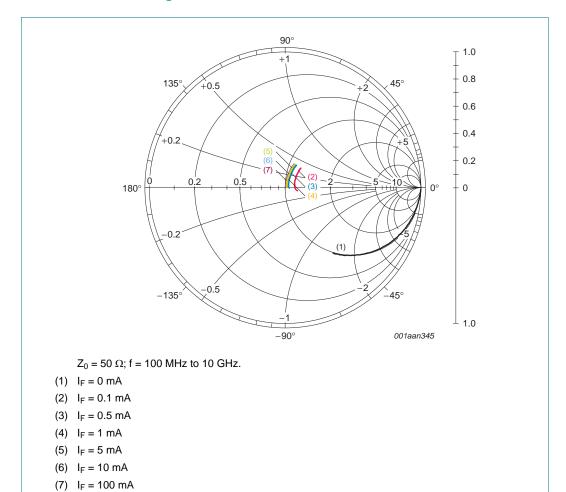
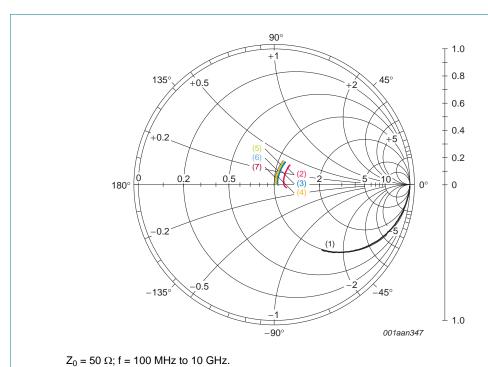
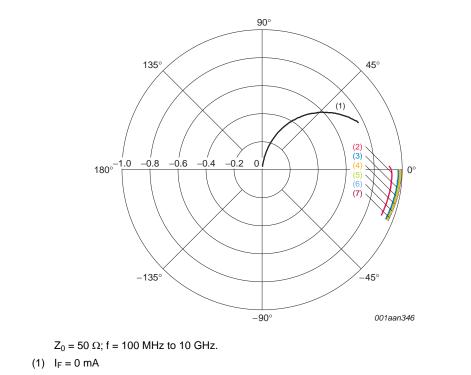


Fig 7. Input reflection coefficient (S<sub>11</sub>); typical values



- (1)  $I_F = 0 \text{ mA}$
- (2)  $I_F = 0.1 \text{ mA}$
- (3)  $I_F = 0.5 \text{ mA}$
- (4)  $I_F = 1 \text{ mA}$
- (5)  $I_F = 5 \text{ mA}$
- (6)  $I_F = 10 \text{ mA}$
- (7)  $I_F = 100 \text{ mA}$

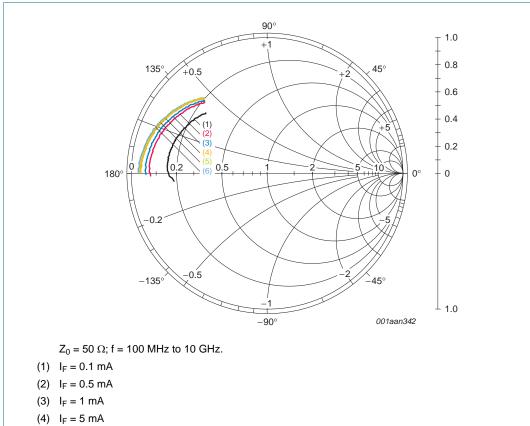
Fig 8. Output reflection coefficient (S<sub>22</sub>); typical values



- (2)  $I_F = 0.1 \text{ mA}$
- (3)  $I_F = 0.5 \text{ mA}$
- (4)  $I_F = 1 \text{ mA}$
- (5)  $I_F = 5 \text{ mA}$
- (6)  $I_F = 10 \text{ mA}$
- (7)  $I_F = 100 \text{ mA}$

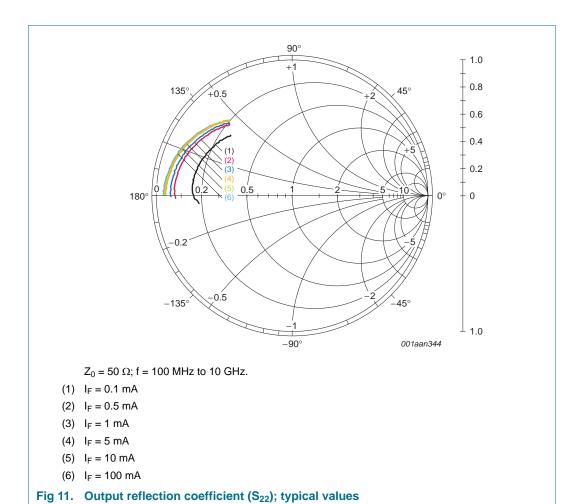
Fig 9. Forward transmission coefficient ( $S_{21}$ ); typical values

## 7.1.2 Diode in parallel configuration



- (5)  $I_F = 10 \text{ mA}$
- (6)  $I_F = 100 \text{ mA}$

Fig 10. Input reflection coefficient ( $S_{11}$ ); typical values



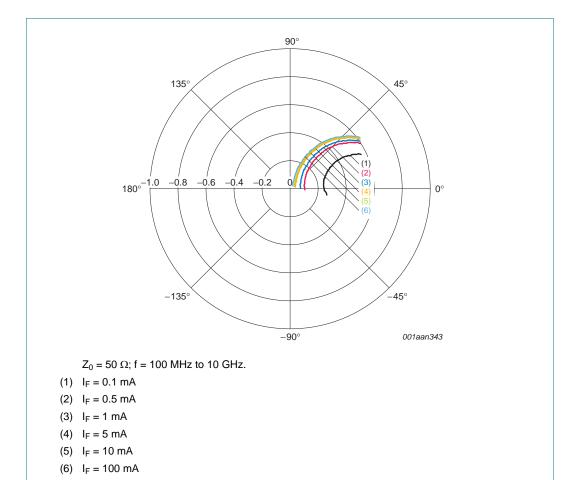


Fig 12. Forward transmission coefficient ( $S_{21}$ ); typical values

# 8. Package outline

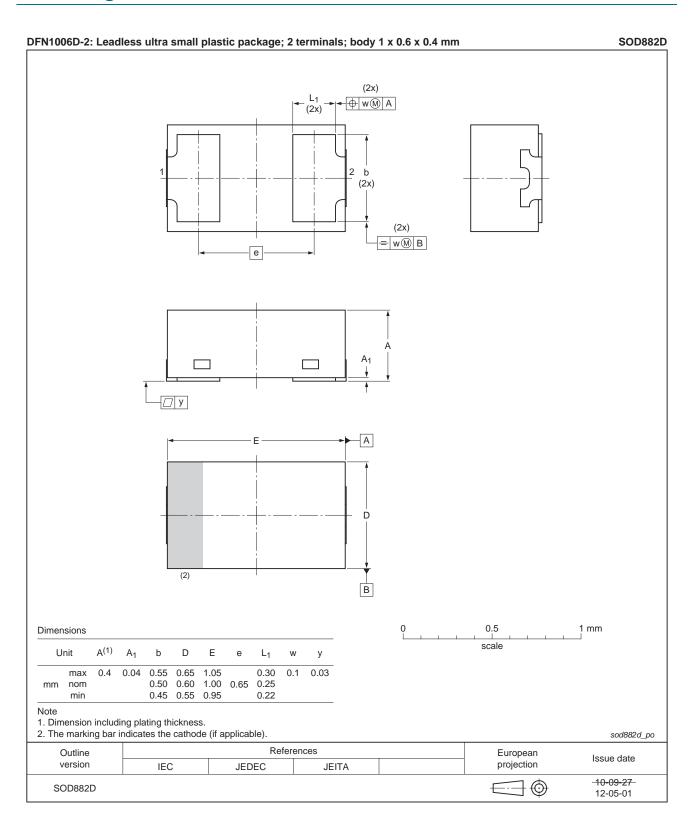


Fig 13. Package outline SOD882D (DFN1006D-2)

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# 9. Abbreviations

Table 7. Abbreviations

Acronym	Description
PIN	P-type, Intrinsic, N-type
SMD	Surface Mounted Device
RF	Radio Frequency

# 10. Revision history

## Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAP55LX v.4	20130806	Product data sheet	-	BAP55LX v.3
Modifications:	<ul><li>Table 1 on p</li><li>Table 2 on p</li><li>Section 4 on</li></ul>	on page 1: Changed package age 1: Changed simplified out age 1: Changed package to S page 2: Update 'Marking' secondage 12: Changed package to page 13: Changed package to page 14: Changed package to	line to SOD882D OD882D ction	
BAP55LX v.3	20110113	Product data sheet	-	BAP55LX v.2
BAP55LX v.2	20101216	Product data sheet	-	BAP55LX v.1
BAP55LX v.1	20070730	Product data sheet	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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#### Silicon PIN diode

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